



#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Features**

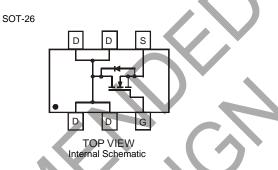
- Low R<sub>DS(ON)</sub>
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 2)

#### **Mechanical Data**

- Case: SOT-26 •
- Case Material Molded Plastic. UL Flammability Rating 94V-0 •
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate) •



TOP VIEW



## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteris	tic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 3)	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 70°C	ID	5.3 4.2	А
Pulsed Drain Current (Note 4)			Ідм	31	A

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 3)	PD	1.12	W
Thermal Resistance, Junction to Ambient $T_A = 25^{\circ}C$ (Note 3)	R <sub>0JA</sub>	111	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

1. No purposefully added lead. Notes:

2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

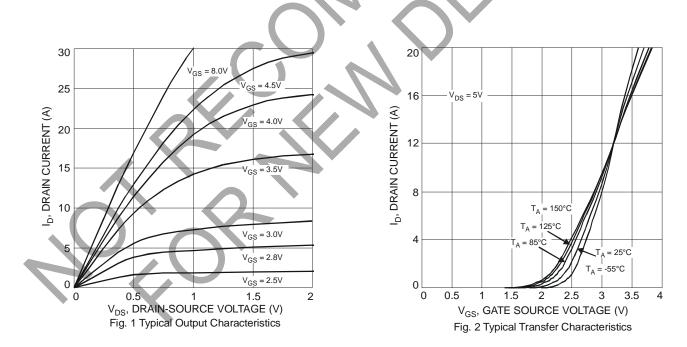
- 3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Repetitive Rating, pulse width limited by junction temperature.



## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

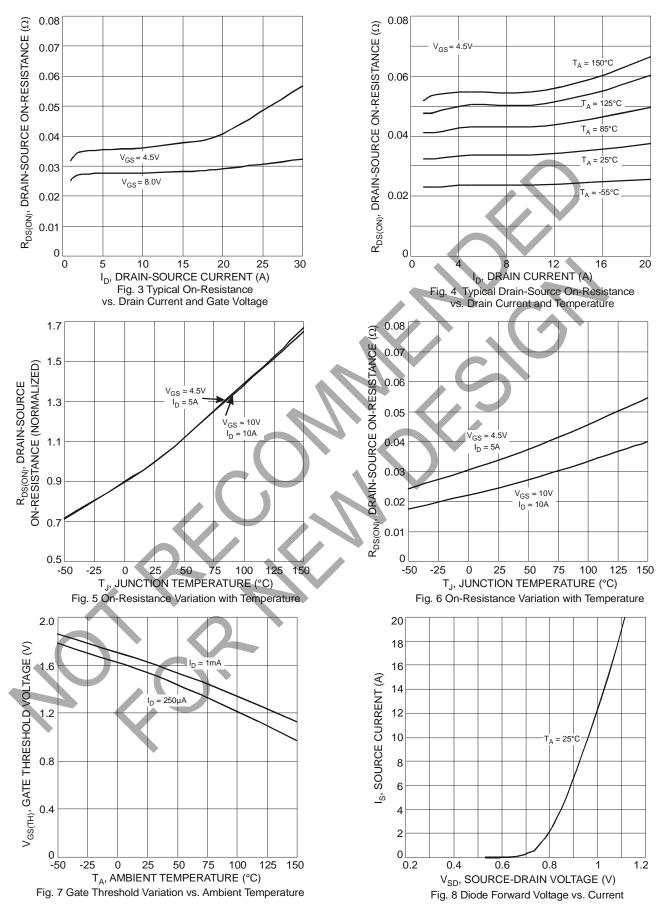
Oberestaristic	Cumhal	Min	True	Max	11	Test Condition
	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					1	1
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	1.0	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	1.5	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
		-	22	27		$V_{GS} = 10V, I_D = 7A$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		32	40	mΩ	$V_{GS} = 4.5V, I_D = 5.6A$
Forward Transfer Admittance	Y <sub>fs</sub>	-	10	-	S	$V_{DS} = 5V, I_D = 7A$
Diode Forward Voltage	V <sub>SD</sub>	-	0.75	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	Ciss	-	404	-	pF	
Output Capacitance	Coss	-	52		pF	V <sub>DS</sub> =15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	-	45	-	pF	T = T.000H2
Gate Resistance	Rg	-	1.51	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg	-	9.2	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	-	1.2	-	nC	V <sub>GS</sub> =10V, V <sub>DS</sub> = 15V, ID =5.8A
Gate-Drain Charge	Q <sub>gd</sub>	- 4	1.8		nC	
Turn-On Delay Time	t <sub>D(on)</sub>		3.41	-	ns	
Turn-On Rise Time	tr	-	6.18	-	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,
Turn-Off Delay Time	t <sub>D(off)</sub>		13.92	-	ns	$R_L = 2.6\Omega, R_G = 3\Omega$
Turn-Off Fall Time	tf	-	2.84	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect. 6. Guaranteed by design. Not subject to production testing.





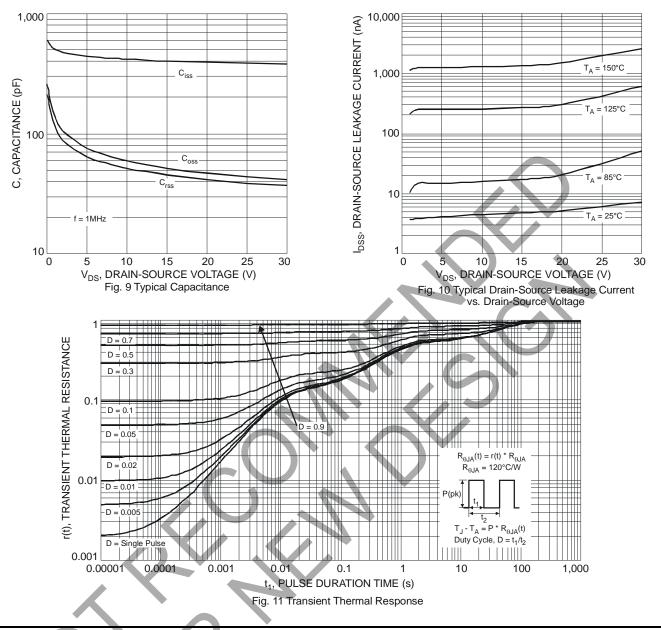
#### NOT RECOMMENDED FOR NEW DESIGN USE DMG6402LVT





### NOT RECOMMENDED FOR NEW DESIGN USE DMG6402LVT

## DMG6402LDM

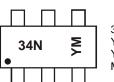


## Ordering Information (Note 7)

Part Numb	er	Case	Packaging
DMG6402LD	Л-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## Marking Information



34N= Product Type Marking Code YM = Date Code Marking

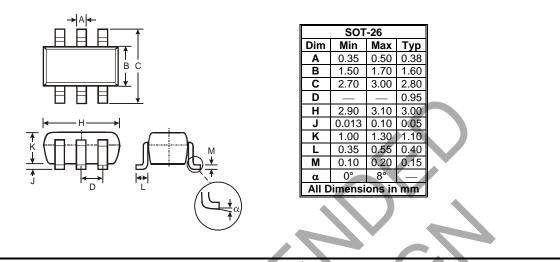
Y = Year (ex: V = 2008)

M = Month (ex: 9 = September)

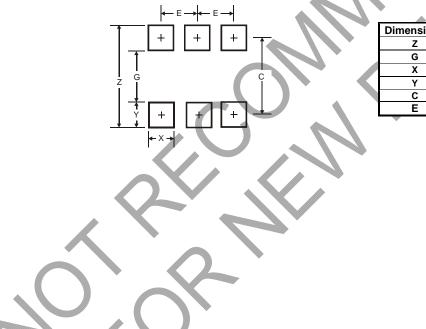
Date Code Key												
Year	2008		2009	2010		2011	2012	2	2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Package Outline Dimensions



# Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
С	2.40
E	0.95



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